

# Soft X-ray detectors at European XFEL

# Andreas Koch European XFEL, WP-75, Detector Development 26.1.2012



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### Specific RIXS requirements (dispersive imaging):

- Dispersive axis: pixel size down to 10  $\mu m,$  even smaller.
- Axis for angular coverage of incoming radiation: more pixels or larger pixel size, i.e. rectangular pixel (aspect ratio x2 ... x10).



## **Overview of detector development efforts / Motivation**



- Baseline detector at XFEL for low energy applications is the DSSC detector (DEPFET Sensor with Signal compression) Full scale, full commissioned version is delayed to 2017.
- <u>Day-1 detector</u> in 2015 for SPS, SQS is needed.
   Small pixel size down to 50 µm is an additional requirement.
   Possible solutions and options are presented.
- A phase 2 detector
  - with enhanced performance is under discussion.

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### Low energy detector alternatives

Market scan July – December 2011. 18 companies and laboratories contacted. 5 contacts are closer investigated.



European	etectors for RIXS					
XFEL	Requirements low energy detector XFEL	DSSC	CS-PAD	pn CCD MPI	Commercial CCD, Cmos, < 15 keV	6 Commercial CCD, Cmos, > 15 keV
	For SCS, SQS	XFEL baseline	Operationa	al at LCLS	Comm	nercial
Technology		DEPFET hybrid	hybrid	CCD	e.g. Roper CCD deep depleted PIXIS-XO	e.g. Dexela 2930MAM mammography
Pixel size	10100s μm	204x236 mm <sup>2</sup> , hex.	110 μm	75µm	13 μm	74.8 μm
Detector size	1kx1k or rectangular	1kx1k	1516x1516 or smaller	1kx1k central hole		29x30 cm <sup>2</sup>
Tiling	central hole	Yes, with central hole	Yes, multiple tiles	2 tiles		4 tiles
Quantum eff./ sensor thickn.	> 80%	>80% @0.4-10 keV 60% at 0.25 eV	500 μm Si	>80% @ 0.3-12 keV	100 μm Si	70% @ 20 keV
Energy range	0.25 – 3 keV	0.5 – 4 keV	<1 –10 keV, opt. 8 keV nominal	0.05-24 keV	0.03-10 keV (Roper)	> 18 keV,
Dynamic range	10 <sup>3</sup> 10 <sup>4</sup>	10 <sup>4</sup>	10 <sup>3</sup> -10 <sup>4</sup>	10 <sup>3</sup>		10 <sup>3</sup> -10 <sup>4</sup>
Noise / noise equ. signal	Single photon sensitivity	1 keV rms	1 keV rms	2 el. rms	2 el. rms	1000 el. estimated
Frame rate	4.5 MHz, 2700 im., 10 bursts	4.5 MHz, 576 images dig. on-chip	120 Hz	200 Hz	2 Hz (Roper) 5 Hz (4x4)	26 Hz
Costs					$\approx 60$ keuros	$\approx$ 45 keuros
Product full spec		2017	?	2015	commercial	commercial
Risks		Calibration, Delay				
Remarks	Specific needs for dispersive	ongoing	to be rebuilt option low energy	to be rebuilt	For vacuum operation	With scintillator

Dete	ectors for RIXS						
European Benchmarking							
	LBNL FS-CCD	XCAM / SACLA	Desy / RAL	Photonic Science	Cornell / SLAC / ESRF	Phase 2 development ?	
	Development projects other labs, companies XFEL						
Technology	Frame transfer CCD, back- illuminated	CCD open electrode, Riken design (MPCCD)	MAPS, Cmos	New Cmos design, back-illum.	sCmos Fairchild (back-illum. in preparation)	3D Cmos, bump bonded sensor, 65 nm SOI	
Pixel size	30 µm	40 µm	25-30 μm	15 μm	6.5 μm	50–100 μm	
Detector size	1kx1k, monol., option hole	1kx1k, 4 tiles, central hole	20x20 cm <sup>2</sup> , hole, 4 tiles	4kx4k, monolithic	2kx2k, monolithic	1kx1k or larger, tiles	
Tiling	Several mm gaps if tiled	Yes	2 side buttable	Yes, with gaps	no	4 side butt? es	
Quantum eff. / sensor thickness	200 µm Si	20% @ 10 keV 40 μm Si	95% @ 1 keV 12 μm Si	15 μm Si	? Waiting to mailor	Si ser crudit.bd.	
Energy range	0.25-8 keV	0.3-10 keV	0.25-1 keV	To be defined	?	0.2-20 keV	
Dynamic range	10 <sup>3</sup> -10 <sup>4</sup>	10 <sup>3</sup> -10 <sup>4</sup>	10 <sup>6</sup> , 3 gains	10 <sup>4</sup>	104	10 <sup>6</sup> , 4 gains	
Noise / noise equ. signal	30-40 el. rms	20 el.rms	15 el. rms 50 eV rms	4 el. rms	2.5 el. rms	200 eV rms	
Frame rate	100 Hz	10 Hz	120 Hz	10 Hz	17 Hz (34 Hz for 1k)	4.5 MHz, 2700 images, digital	
Costs	rel. low	rel. low					
Product, full perf.	2014	2013	2014	1.5-2 years	?	4-5 years	
Risks			Noise, delay	Consortium needed		3d integration	
Remarks	Ongoing, ≈15 cameras	Riken prototype, options possible	Ongoing project for Flash	Proposal	<ul><li> Project idea</li><li> scintillator ?</li></ul>	Proposal - high-end	



### Other specifications, open points

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- Radiation hardness
- Medium term stability (temperature, voltages, charge effects)
- Local electron / hole plasma effects in the Si sensor
- Calibration
- Data acquisition
- **a**.o.





# **XFEL** DSSC 1 MPixel Detector Module



### **Key Detector Parameters**

- Goal: Single photon sensitivity
  5 σ @1 keV and 4.5 MHz
- Energy range 0.5 – 6 (25) keV
- Dynamic range
  - > 6000 photons/pixel/pulse @1 keV
- Single photon sensitivity

5 σ @ 1 keV (5 MHz)

- 5 σ @ 0.5 keV (≤ 2.5 MHz)
- Number of storage cells 576
- Smallest detector unit "ladder 128 x 512 pixels
- 4 ladders built on quadrant
- 4 quadrants = 1k x 1k detector

# **DSSC - DEPFET Sensor with Signal** XFEL Compression



### **Pixel Cell**

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- DEPFET combined with Silicon drift detector
- $\rightarrow$  scalable pixel size
- Low noise
- $\rightarrow$  Good energy response down to 500 eV

# **Pixel Geometry**





- Hexagonal pixels
- $\rightarrow$  more homogeneous drift field
- $\rightarrow$  minimize charge collection time
- $\rightarrow$  less charge sharing (split events)
- Per pixel ADC/digital storage pipeline
- $\rightarrow$  no charge leakage
- 576 9 bit SRAM storage cells per pixel

# Fast X-ray Pixel Detectors for Synchrotron Radiation Light Sources





### **Devis Contarato**

on behalf of the EG/ALS Detector Engineering Group:

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... and many more contributors



13th International Workshop on Radiation Imaging Detectors

3<sup>th</sup> – 7<sup>th</sup> July 2011 Zurich and Villigen PSI Switzerland

# **Readout architecture options**





Devis Contarato

Fast X-ray Pixel Detectors for Light Sources

IWORID 2011 Zurich, July 7, 2011



# Prototype Fast CCD

- generation direct soft X-ray detector 1<sup>st</sup> developed by LBNL in collaboration with ANL:
  - multi-port
  - 200 µm thick, fully depleted
  - back-illuminated
- 480×480 pixels, 30 µm pitch
- 96 analog outs, quasi-Column Parallel readout (10 column MUX)
- 200 fps readout rate





- Performance:
  - 900000 e<sup>-</sup>/pixel full well >
  - 250 eV single photon resolution
  - PSF < 1 pixel

[P. Denes et al., Rev. Sci. Instruments 80, 083302 (2009)]



**Devis Contarato** 

Fast X-ray Pixel Detectors for Light Sources

Zurich, July 7, 2011



# 1k Frame-Store CCD



- 1920×960 pixels, 30 µm pitch , sensor based on Fast CCD design and cFCCD detector head
  - 960×960 pixels X-ray sensitive area in frame transfer mode (200 fps) >
  - 1920×960 pixels X-ray sensitive area in full imaging mode (100 fps) >
- 192 analog outputs (quasi-CP readout), 12 custom readout ASICs, raw data bandwidth 400 MB/s ٠
- Full detector systems being developed under Recovery Act funding, to be delivered in 2011 (8 ٠ systems @ ALS, 2 systems @ APS, interest from SSRL/LCLS and NSLS-II)

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Fast X-ray Pixel Detectors for Light Sources

Zurich, July 7, 2011



### Fairchild sCMOS



Parameter	sCMOS	Interline CCD	EMCCD
Sensor Format	5.5 megapixel	1.3 to 4 megapixel	0.25 to 1 megapixel
Pixel Size	6.5 µm	6.45 to 7.4µm	8 to 16 µm
Read Noise	< 2 e <sup>-@</sup> 30 frames/s	4 -10 e-	< 1e <sup>-</sup> (with EM gain)
Full Frame Rate (maximum)	100 frames/s @ full resolution	3 to 16 frames/s	~30 frames/s
Quantum Efficiency (QE)	60%	65%	90% 'back-illuminated' 65 % 'virtual phase'
Dynamic Range	> 16,000:1 (@ 30 frames/s)	~ 3,000:1 (@ 11 frames/s)	8500:1 (@ 30 frames/s with low EM gain)
Multiplicative Noise	None	None	1.41x with EM gain ( <i>effectively</i> halves the QE)



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### European Next steps, opportunities

#### LBNL

- Prototype testing at ALS in March. 0
- MPI
- 1 Mpx sensor available at HLL Munich. 0
- SLAC / Cornell / ESRF

New project ideas will be followed up:

- Modified CS-PAD.
- Fairchild sCMOS, back-illuminated or with scintillator. 0
- .... and look to future trends, a phase 2 project ?
  - Contacts and discussions foreseen.  $\mathbf{O}$
  - Carefully understand:
    - detector technology evolution & scientific requirements. Through Silicon Vias, TSVs, to
  - Identify partners, interests, costs. Ο



link DRAM chips, by IBM

